# XN04505 (XN4505)

# NPN epitaxial planer transistor

For general amplification (Tr1) For amplification of low frequency output (Tr2)

# Features

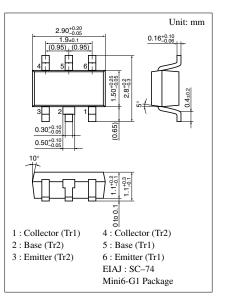
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

## Basic Part Number of Element

• 2SD0601A(2SD601A) + 2SD1328

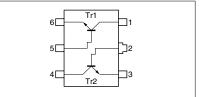
ŀ	Parameter	Symbol	Ratings	Unit	
Tr1	Collector to base voltage	V <sub>CBO</sub>	60	V	
	Collector to emitter voltage	V <sub>CEO</sub>	50	V	
	Emitter to base voltage	V <sub>EBO</sub>	7	V	
	Collector current	I <sub>C</sub>	100	mA	
	Peak collector current	I <sub>CP</sub>	200	mA	
Tr2	Collector to base voltage	V <sub>CBO</sub>	25	V	
	Collector to emitter voltage	V <sub>CEO</sub>	20	V	
	Emitter to base voltage	V <sub>EBO</sub>	12	V	
	Collector current	I <sub>C</sub>	0.5	А	
	Peak collector current	I <sub>CP</sub>	1	А	
Overall	Total power dissipation	P <sub>T</sub>	300	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### Absolute Maximum Ratings (Ta=25°C)



# Marking Symbol: DZ

#### Internal Connection



Note) The Part number in the Parenthesis shows conventional part number.

# Electrical Characteristics (Ta=25°C)

• Tr1

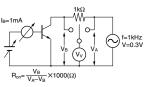
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	60			V
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 2mA, I_{\rm B} = 0$	50			V
Emitter to base voltage	V <sub>EBO</sub>	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	7			V
	I <sub>CBO</sub>	$V_{CB} = 20V, I_E = 0$			0.1	μΑ
Collector cutoff current	I <sub>CEO</sub>	$V_{CE} = 10V, I_B = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10V, I_C = 2mA$	160		460	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 10 {\rm mA}$		0.1	0.3	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 1MHz$		3.5		pF

#### • Tr2

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	25			v
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 1 {\rm mA},  I_{\rm B} = 0$	20			v
Emitter to base voltage	V <sub>EBO</sub>	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	12			V
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 25V, I_E = 0$			0.1	μA
	h <sub>FE1</sub>	$V_{CE} = 2V, I_C = 0.5A^{*1}$	200		800	
Forward current transfer ratio	h <sub>FE2</sub>	$V_{CE} = 2V, I_C = 1A^{*1}$	60			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 0.5 {\rm A}, I_{\rm B} = 20 {\rm mA}$		0.13	0.4	v
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 0.5 {\rm A}, I_{\rm B} = 20 {\rm mA}$			1.2	v
Transition frequency	f <sub>T</sub>	$V_{CB} = 10V, I_E = -50mA$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 1MHz$		10		pF
ON Resistance	R <sub>on</sub> <sup>*2</sup>			1.0		Ω

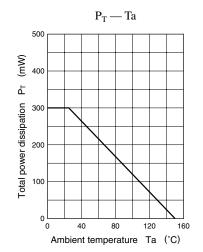
\*1 Pulse measurement

\*2 Ron test circuit





#### Common characteristics chart



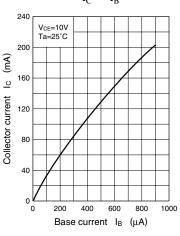
V<sub>CE</sub>=10V

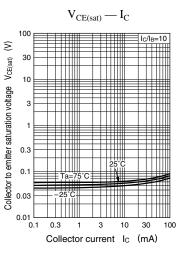
25°C

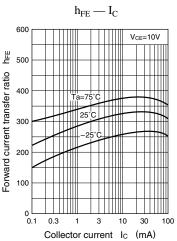
1.2

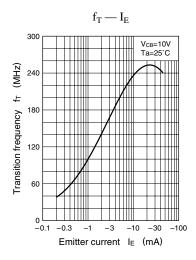
1.6 2.0

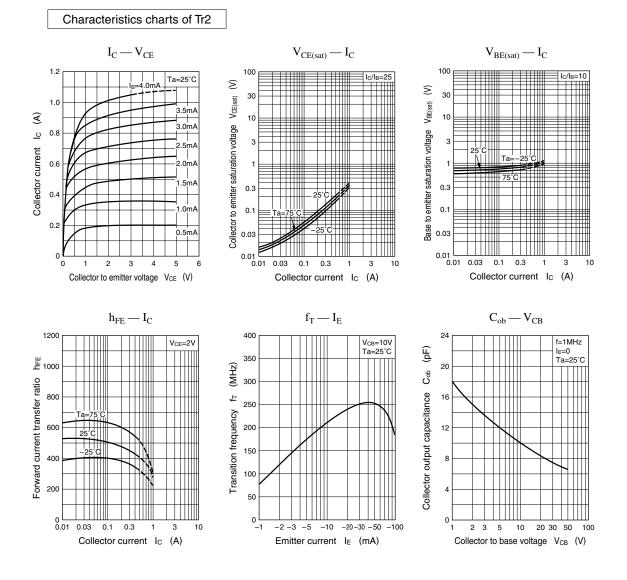
#### Characteristics charts of Tr1 $I_B - V_{BE}$ $I_C - V_{BE}$ $I_C - V_{CE}$ 60 1200 240 Ta=25°C V<sub>CE</sub>=10V I<sub>B</sub>=160μA Ta=25°C 1000 200 50 (mA) Collector current Ic (mA) 140µA (h) 800 40 160 120µA Collector current Ic <u>\_</u> 100µA Base current 25°C 30 600 120 ł ł ł 80µA Ta=75°C 20 400 80 60µ A 40µA 200 40 10 20µA 0 ' 0 0 0.2 0.4 0.6 0.8 1.0 0.4 0 2 4 6 8 10 0 0.8 Collector to emitter voltage VCE (V) Base to emitter voltage VBE (V) Base to emitter voltage VBE (V) $I_C - I_B$ V<sub>CE(sat)</sub> - I<sub>C</sub> 240 100 600 $I_C/I_B=10$ V<sub>CE</sub>=10V Ta=25°C Σ 30 ЧE 500 200 10 160 400 =75 3











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